

Appl. No. 10/773,383  
Office Action mailed 04/06/2007

In the Claims

Claims 1-31 [canceled].

32. [Previously Presented] A temperature sensing apparatus fabrication method comprising:

forming a cavity in an electronic device workpiece;

providing a temperature sensing device within the cavity and in a configuration to sense temperature of the electronic device workpiece;

supporting the temperature sensing device using the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device.

33. [Previously Presented] The method according to claim 32 wherein the electrically coupling comprises wire bonding the electrical interconnect and the temperature sensing device.

34. [Cancelled].

35. [Previously Presented] The method according to claim 32 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

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36. [Previously Presented] The method according to claim 32 wherein the forming the cavity comprises isotropically etching the electronic device workpiece.

37. [Original] The method according to claim 32 further comprising forming the temperature sensing device.

38. [Original] The method according to claim 37 wherein the forming the temperature sensing device comprises forming a resistance temperature device.

39. [Original] The method according to claim 32 further comprising electrically coupling the electrical interconnect with external circuitry.

40. [Original] The method according to claim 32 further comprising electrically coupling the temperature sensing device with an edge of the electronic device workpiece using the electrical interconnect.

41. [Original] The method according to claim 32 wherein the providing the electrical interconnect comprises forming a conductive trace.

42. [Original] The method according to claim 32 further comprising contacting the electrical interconnect with the temperature sensing device.

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43. [Previously Presented] The method according to claim 32 wherein the sensing comprises sensing temperature of the electronic device workpiece comprising a semiconductive wafer.

Claims 44-52 [canceled].

53. [Previously Presented] A temperature sensing apparatus fabrication method comprising:

providing an electronic device workpiece;  
forming a plurality of temperature sensing devices over the electronic device workpiece, the temperature sensing devices being configured to sense temperature in three dimensions of the electronic device workpiece.

54. [Previously Presented] The method according to claim 53 further comprising:  
providing an electrical interconnect upon the electronic device workpiece; and  
electrically coupling the electrical interconnect with at least one of the temperature sensing devices.

55. [Original] The method according to claim 54 wherein the providing the electrical interconnect comprises forming a conductive trace.

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56. [Previously Presented] The method according to claim 54 wherein the electrically coupling comprises wire bonding the electrical interconnect and the at least one of the temperature sensing devices.

57. [Previously Presented] The method according to claim 54 wherein the electrically coupling includes contacting the electrical interconnect and the at least one of the temperature sensing devices.

58. [Previously Presented] The method according to claim 53 further comprising:  
forming a cavity in the electronic device workpiece; and  
providing at least one of the temperature sensing devices within the cavity.

59. [Original] The method according to claim 58 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

60. [Previously Presented] The method according to claim 53 wherein the forming comprises forming the temperature sensing devices individually comprising a resistance temperature device.

61. [Cancelled].

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62. [Previously Presented] A temperature sensing apparatus fabrication method comprising:

supporting a temperature sensing device using an electronic device workpiece;  
providing the temperature sensing device in a temperature sensing relationship with the electronic device workpiece;  
providing an electrical interconnect upon a surface of the electronic device workpiece; and  
electrically coupling the electrical interconnect with the temperature sensing device comprising wire bonding the electrical interconnect and the temperature sensing device.

63. [Cancelled].

64. [Cancelled].

65. [Original] The method according to claim 62 further comprising:  
forming a cavity in the electronic device workpiece; and  
providing the temperature sensing device within the cavity.

66. [Original] The method according to claim 65 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

67. [Previously Presented] The method according to claim 62 further comprising forming the temperature sensing device upon the electronic device workpiece.

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68. [Original] The method according to claim 62 further comprising electrically coupling the electrical interconnect with circuitry external to the electronic device workpiece.

69. [Original] The method according to claim 62 further comprising electrically coupling the temperature sensing device with an edge of the electronic device workpiece using the electrical interconnect.

70. [Original] The method according to claim 62 wherein the providing the electrical interconnect comprises forming a conductive trace.

71. [Previously Presented] A temperature sensing method comprising:  
supporting a plurality of temperature sensing devices using a wafer, and wherein the temperature sensing devices are individually in a temperature sensing relationship with respect to the wafer;

exposing the wafer and the temperature sensing devices to process conditions effective to form at least one electronic device; and

sensing temperature of the wafer in three dimensions of the wafer using the temperature sensing devices during the exposing.

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72. [Previously Presented] The method of claim 71 further comprising adjusting the process conditions responsive to the sensing.

73. [Previously Presented] The method of claim 71 further comprising sensing the temperature of the wafer at a plurality of positions covering substantially an entirety of a surface of the wafer.

74. [Canceled].

75. [Previously Presented] The method of claim 71 wherein the wafer comprises a production wafer, and further comprising forming the at least one electronic device using the wafer during the exposing.

76. [Previously Presented] The method according to claim 32 wherein the electronic device workpiece comprises a silicon wafer.

77. [Previously Presented] The method according to claim 32 further comprising configuring the temperature sensing device to sense the temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

78. [Previously Presented] The method according to claim 53 wherein the providing the electronic device workpiece comprises providing a wafer comprising silicon.

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79. [Previously Presented] The method according to claim 53 wherein the wherein the temperature sensing devices are individually configured to sense the temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

80. [Previously Presented] The method according to claim 62 wherein the electronic device workpiece comprises a silicon wafer

81. [Previously Presented] The method according to claim 62 wherein the temperature sensing device is configured to sense temperature of the electronic device workpiece during fabrication of an electronic device using the electronic device workpiece.

82. [Previously Presented] The method of claim 71 wherein the supporting comprises supporting the temperature sensing devices using the wafer comprising silicon.

83. [Previously Presented] The method of claim 71 wherein the sensing the temperature comprises sensing the temperature of the wafer during fabrication of an electronic device using the wafer.

84. [Previously Presented] A temperature sensing apparatus fabrication method comprising:

providing an electronic device workpiece;

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forming a temperature sensing device over the electronic device workpiece, the forming including providing the temperature sensing device in a temperature sensing relation with the electronic device workpiece;

providing an electrical interconnect upon the electronic device workpiece;

electrically coupling the electrical interconnect with the temperature sensing device;

and

wherein the electrically coupling comprises wire bonding the electrical interconnect and the temperature sensing device.

85. [Canceled].

86. [Canceled].

87. [Previously Presented] A temperature sensing apparatus fabrication method comprising:

forming a cavity in an electronic device workpiece;

supporting a temperature sensing device using the electronic device workpiece, the supporting comprising providing the temperature sensing device within the cavity in a temperature sensing relationship with the electronic device workpiece;

providing an electrical interconnect upon a surface of the electronic device workpiece; and

electrically coupling the electrical interconnect with the temperature sensing device.

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88. [Previously Presented] The method according to claim 87 wherein the forming the cavity comprises anisotropically etching the electronic device workpiece.

89. [Canceled].